

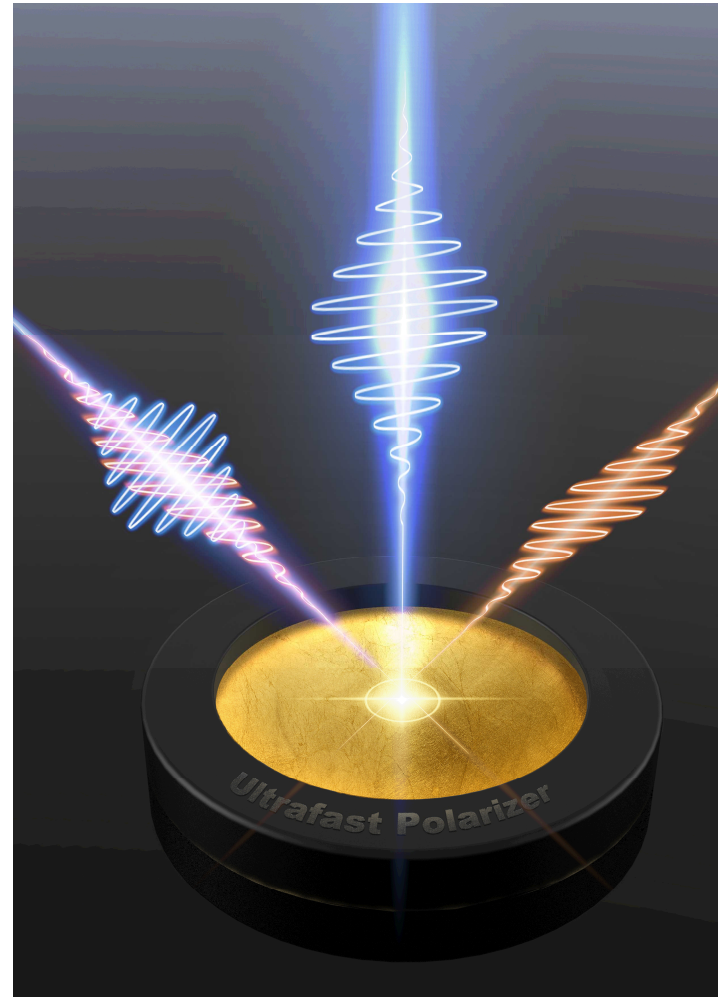


Ultrafast Plasmonics in Oxide and III-V Semiconductors

Yuanmu Yang

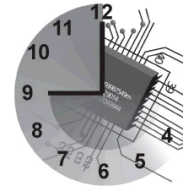
**Sandia National Labs &
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(CINT)**

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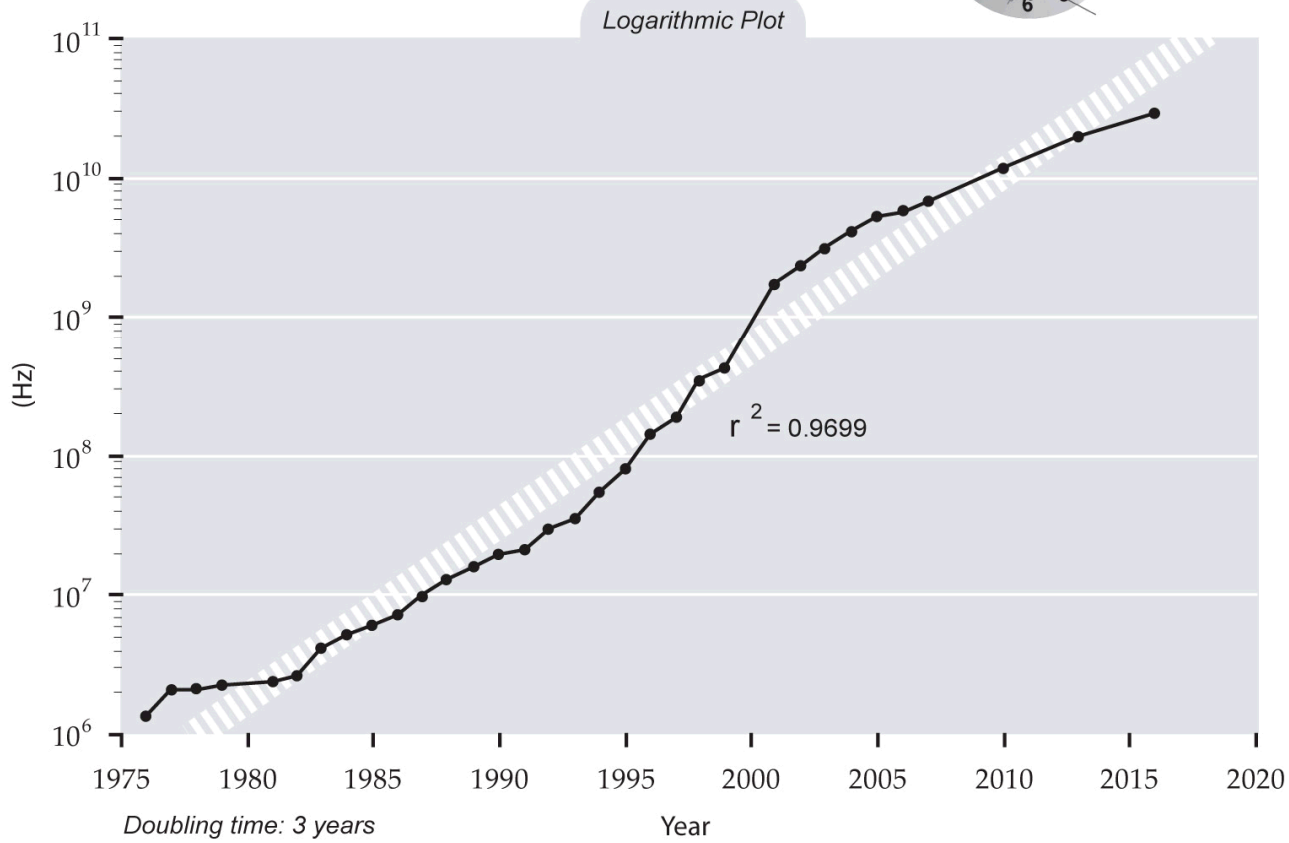




How fast can we process information?



Microprocessor Clock Speed

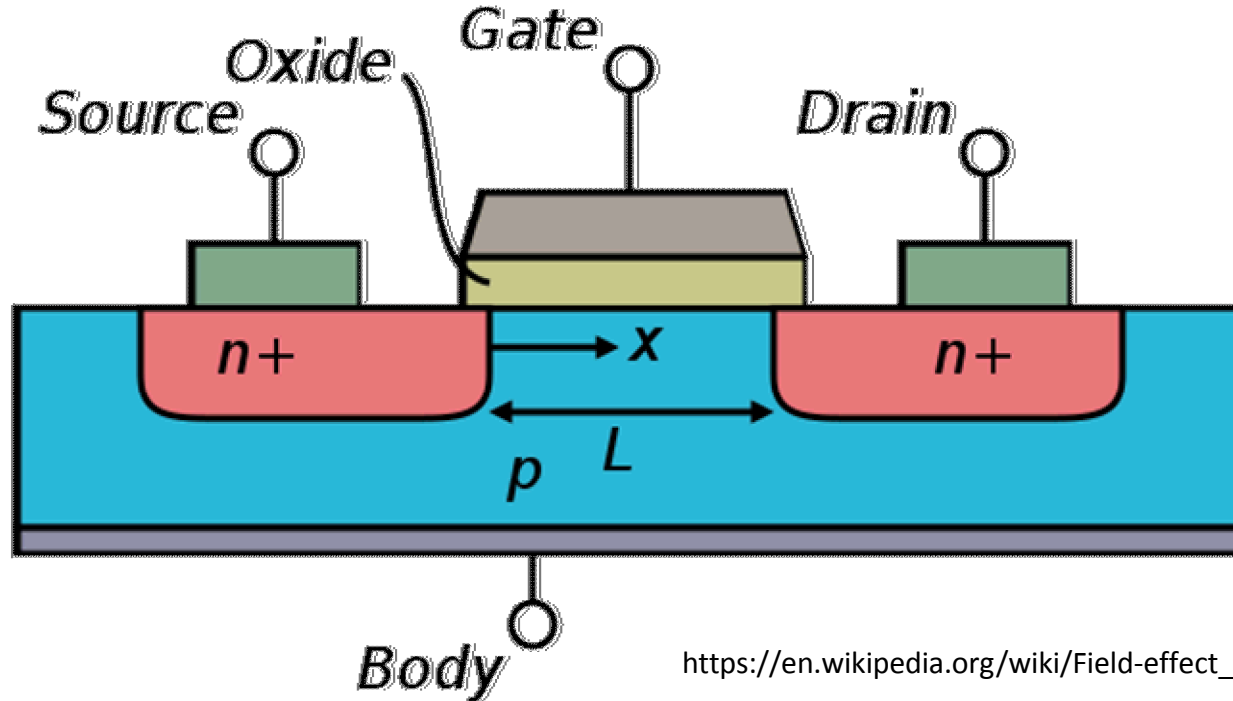


<http://www.singularity.com/charts/page61.html>



How fast can we process information?

Field effect transistor:



https://en.wikipedia.org/wiki/Field-effect_transistor#/media/

Speed limitations:

- **Carrier transit time**
 - It takes time for the carriers to travel
- **RC constant**
 - It takes time to charge up unavoidable capacitors

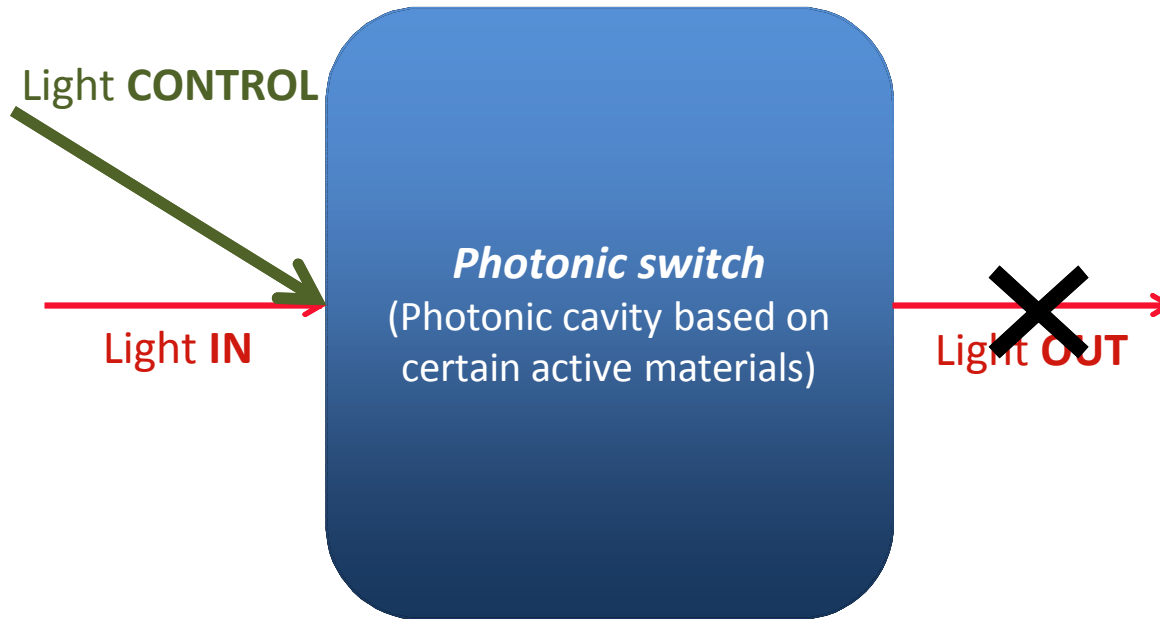
$$f_c = \frac{1}{2\pi RC}$$



Alternatives: All-optical information processing

All-optical information processing:

- **Photon** as an information *switch*.
- **Photon** as an information *carrier*.





Photon as an information switch

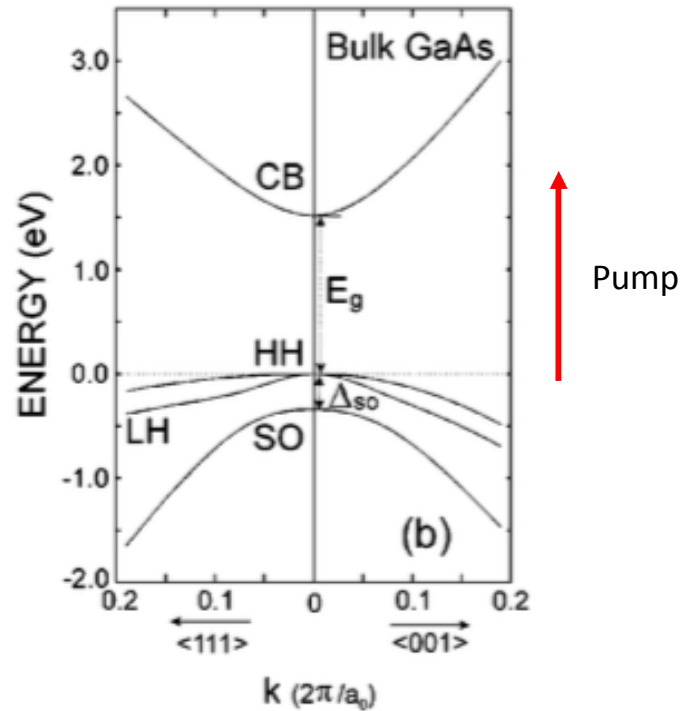
Photon-“create” electrons:

Plasma frequency:

$$\omega_p = \sqrt{ne^2 / \epsilon_0 m^*}$$

Speed limitations:

- Carrier lifetime



Vurgaftmana JAPN (2001)



Photon as an information switch

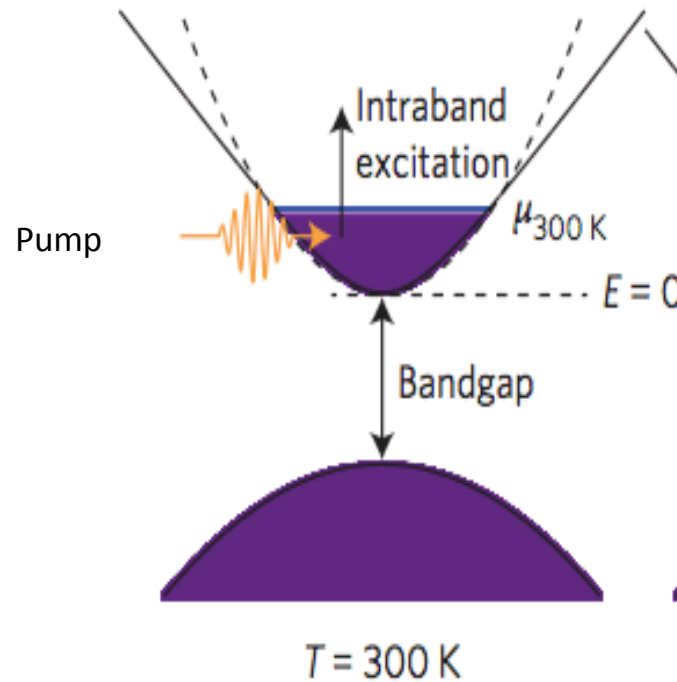
Photon-“perturb” electrons:

Plasma frequency:

$$\omega_p = \sqrt{ne^2 / \epsilon_0 m^*}$$

Speed limitations:

- Hot Carrier lifetime

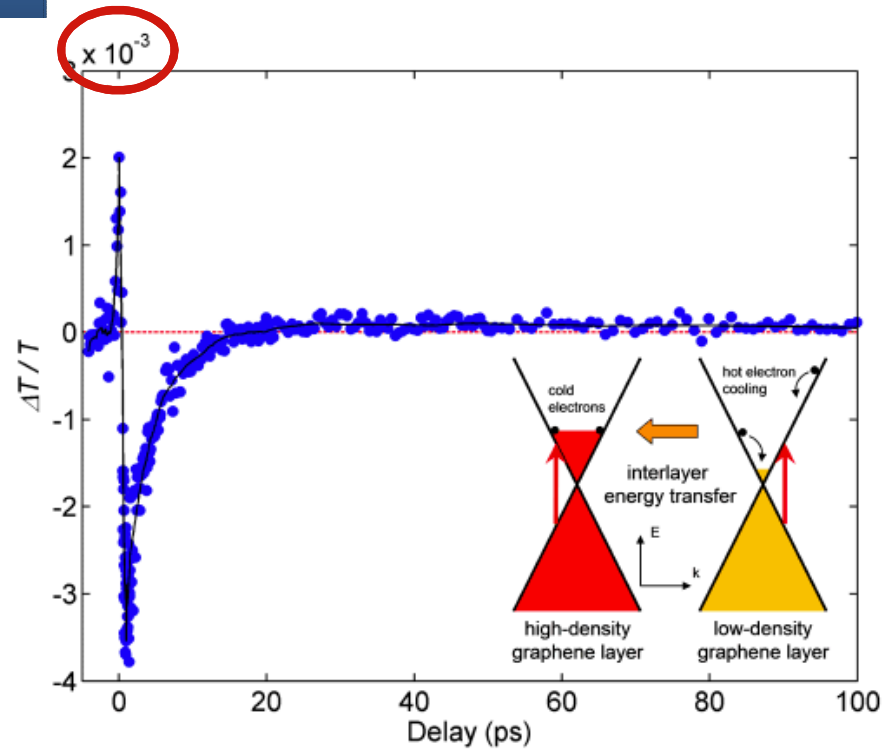
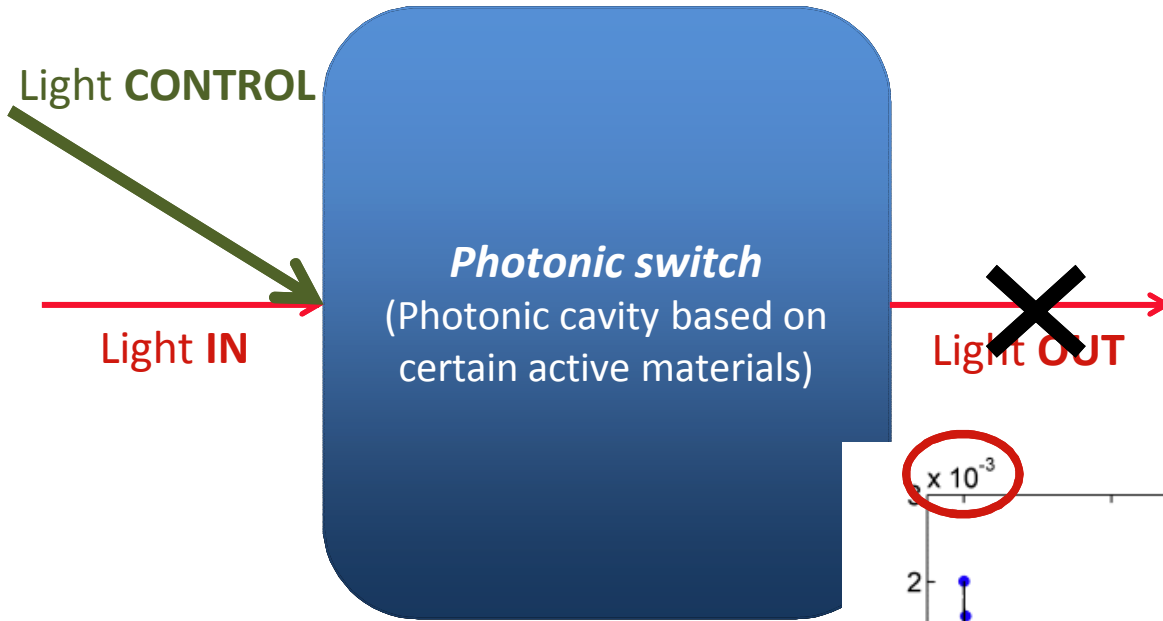


$$m^* = \frac{\hbar^2}{k_{ex}} \cdot \frac{1}{\partial^2 E_n / \partial k^2}$$

Guo et. al., Nat. Photon, (2016)



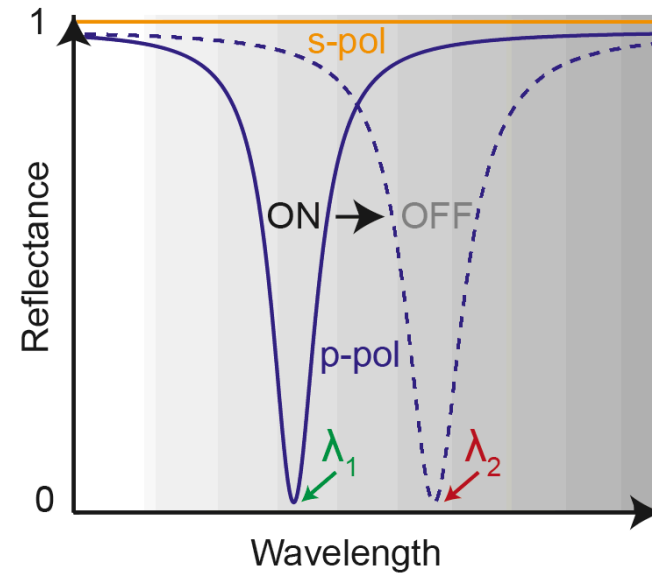
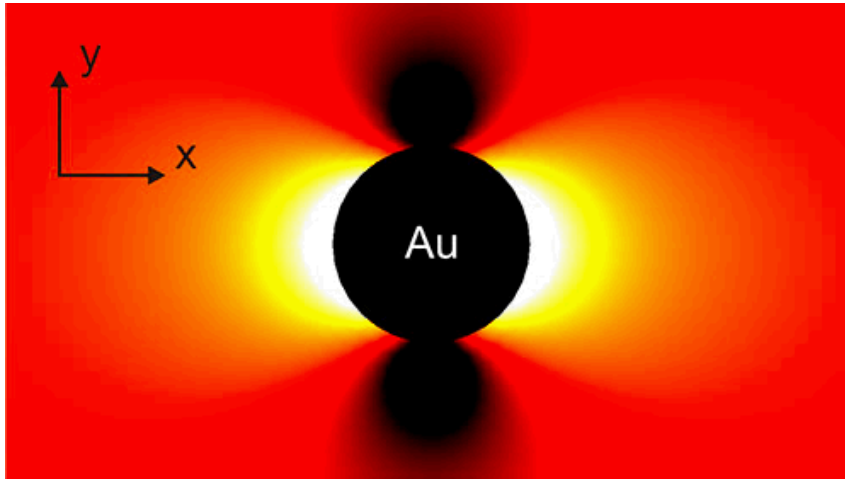
Cavity

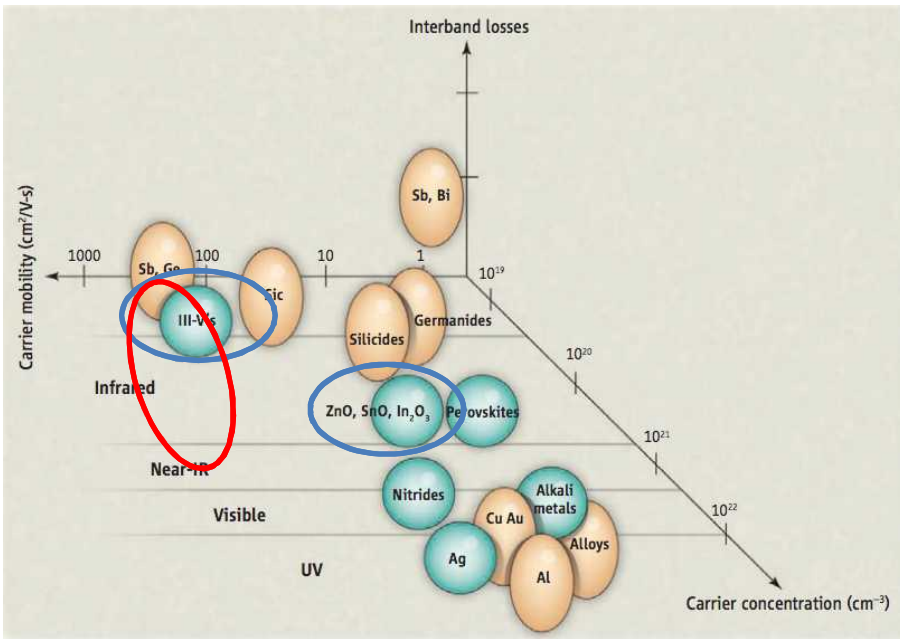




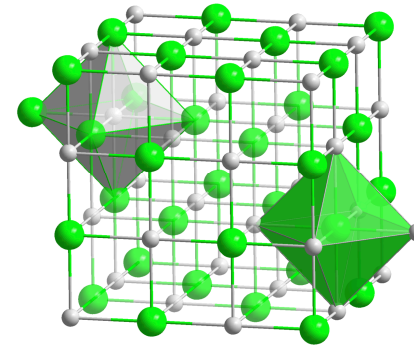
Plasmonic cavity:

- **Enhanced** light-matter interaction.





Boltasseva & Atwater, Science 331, 290 (2011)



<http://chemistry.stackexchange.com/questions/23673/rock-salt-structure>

- Cubic rocksalt lattice (similar to NaCl)
- n-doping (In populates the Cd sublattice with a 3+ charge)

- Doping density can reach $> 10^{20} \text{cm}^{-3}$
- Plasma frequency tunable from near to long IR
- Mobilities in the 100's, sometimes comparable with III-V's.

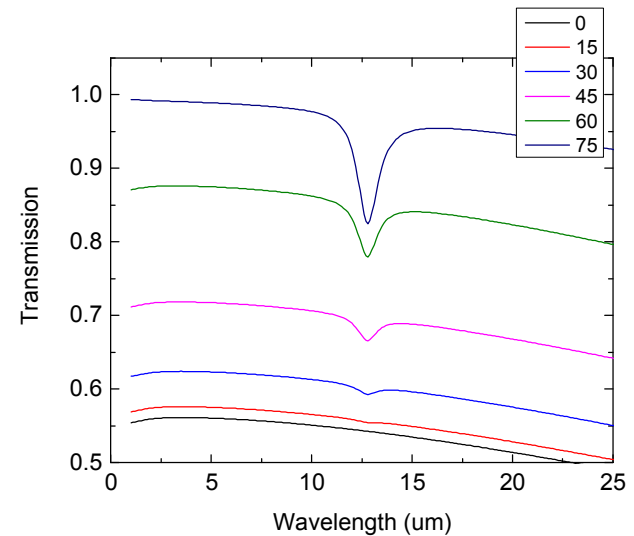
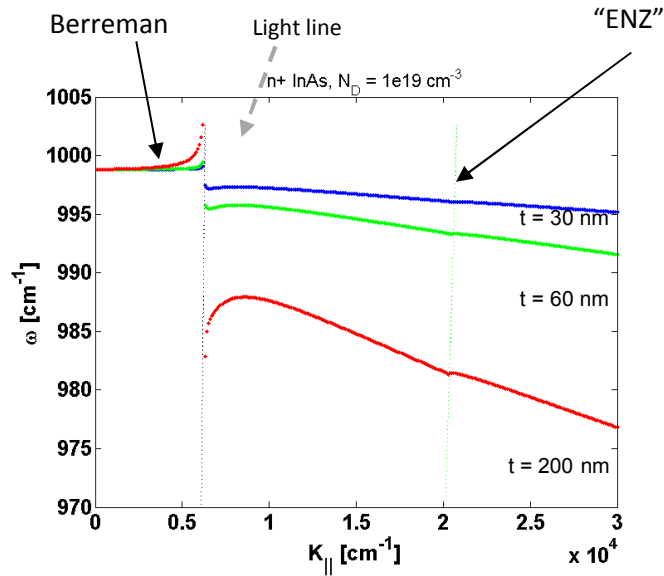
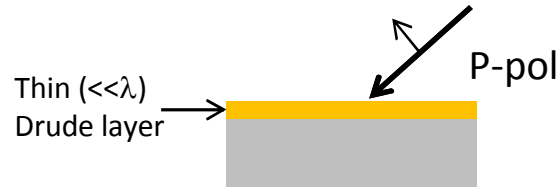
Material	Carriers [cm ⁻³]	Mobility [cm ² /V-s]	$\epsilon_1=0$ [cm ⁻¹]	ϵ_2 at $\epsilon_1=0$	ϵ_2 at $\epsilon_1=-2$
CdO:Dy	9.94×10^{19}	474	2770	0.19	0.30
CdO:Dy	3.70×10^{20}	359	5350	0.13	0.20
AZO (2 wt%) ⁴	7.2×10^{20}	48	6970	0.21	0.39
ITO (10 wt%) ⁴	7.7×10^{20}	36	7122	0.69	1.29

Sachet et. al., Nat. Mat (2015)

J-P Maria, NC State

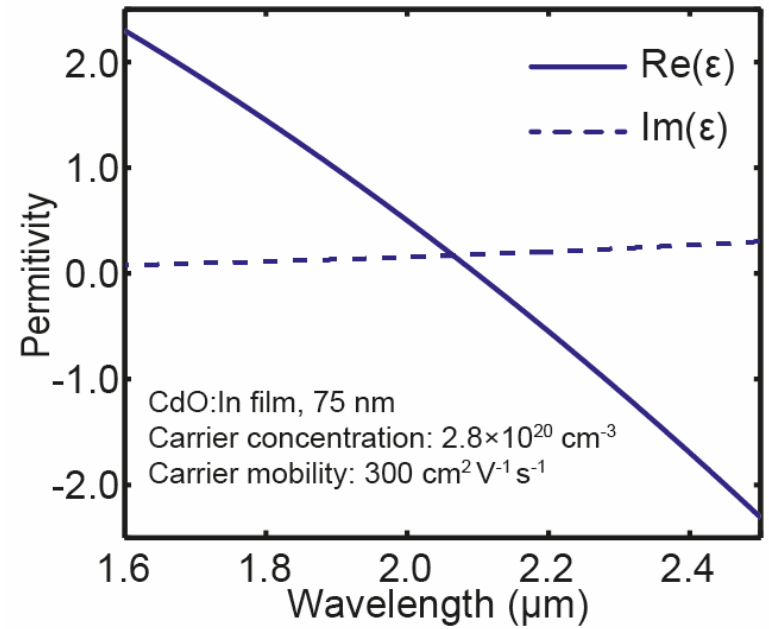
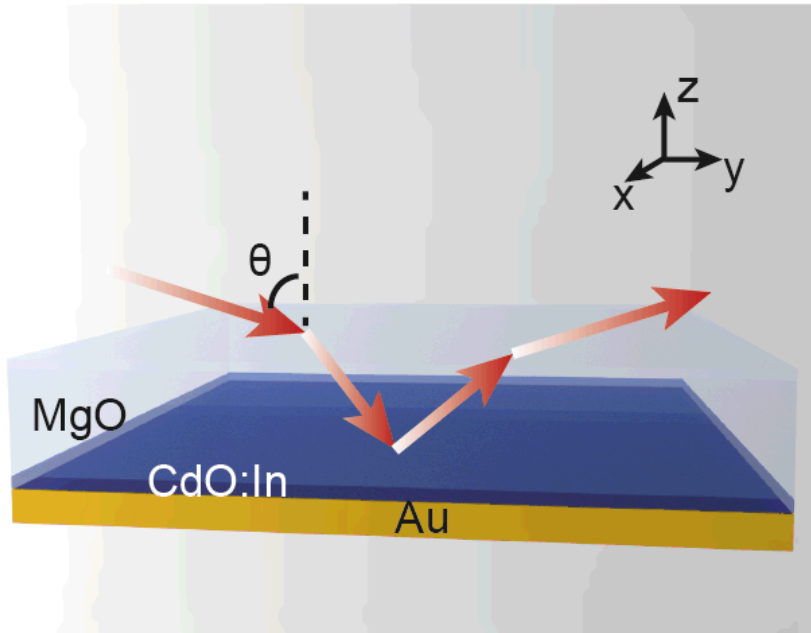


Plasmonic Cavity: "Berreman-mode"



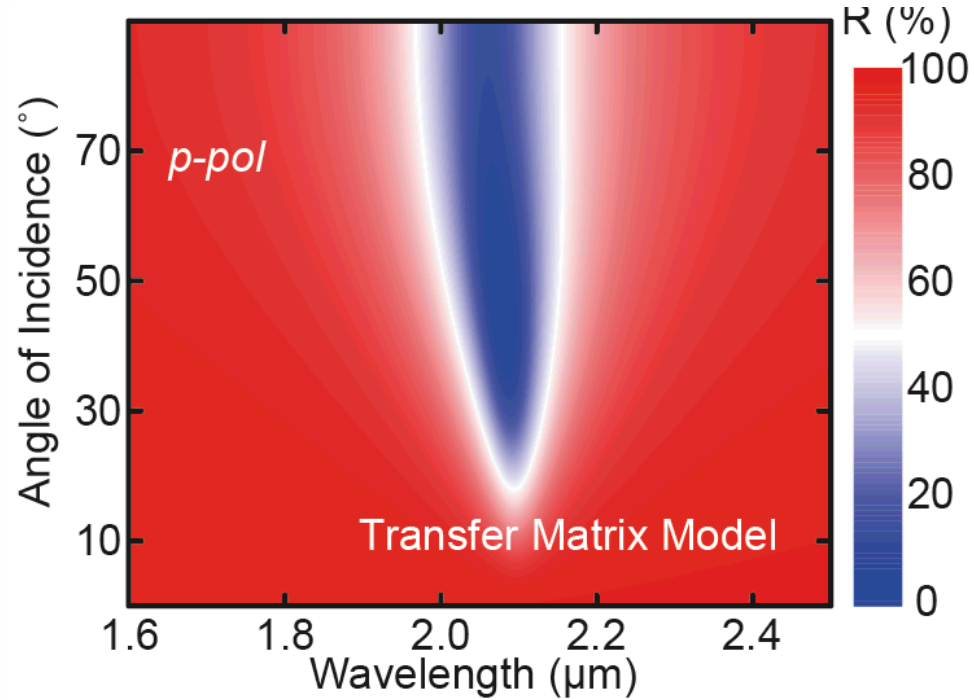
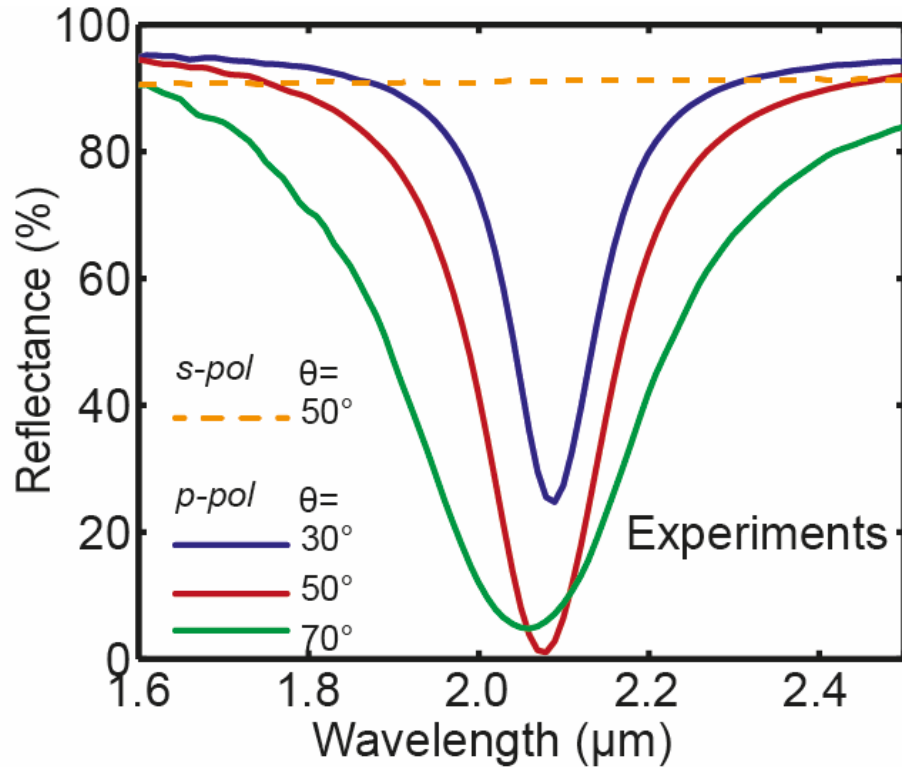


CdO-based Berreman-mode Perfect Absorber





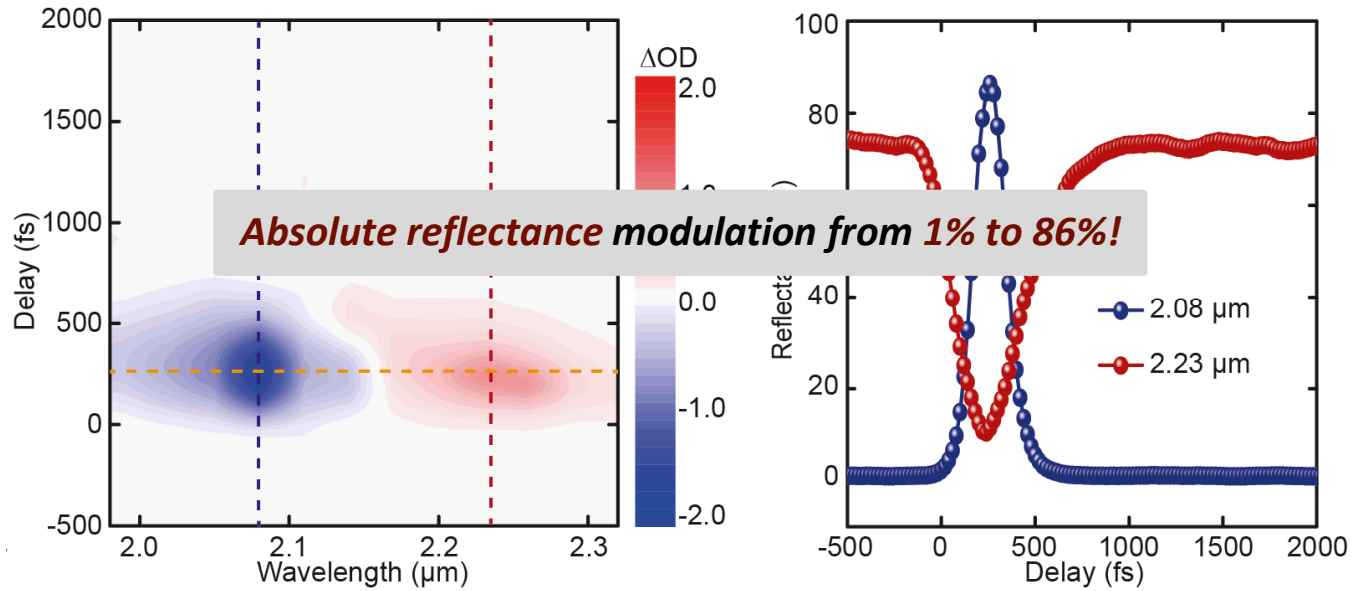
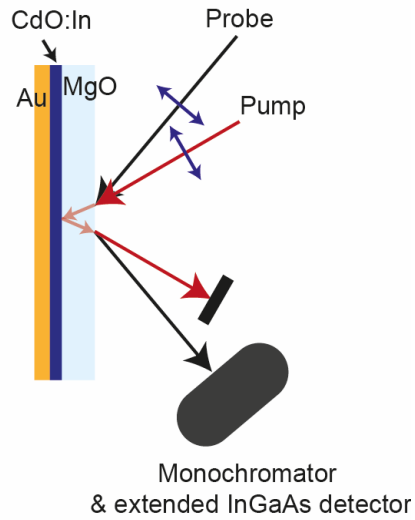
CdO-based Berreman-mode Perfect Absorber



- Berreman-type **perfect absorber** for **p-polarized** incident light at 50 degrees.
- **>90%** reflectance for **s-polarized** light.

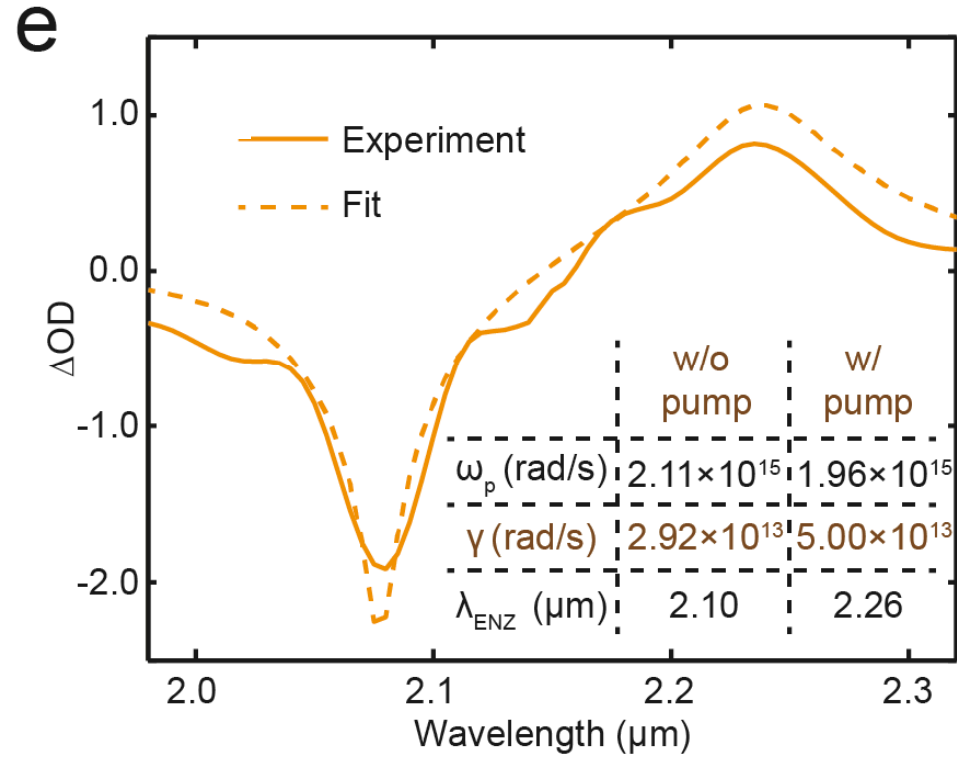
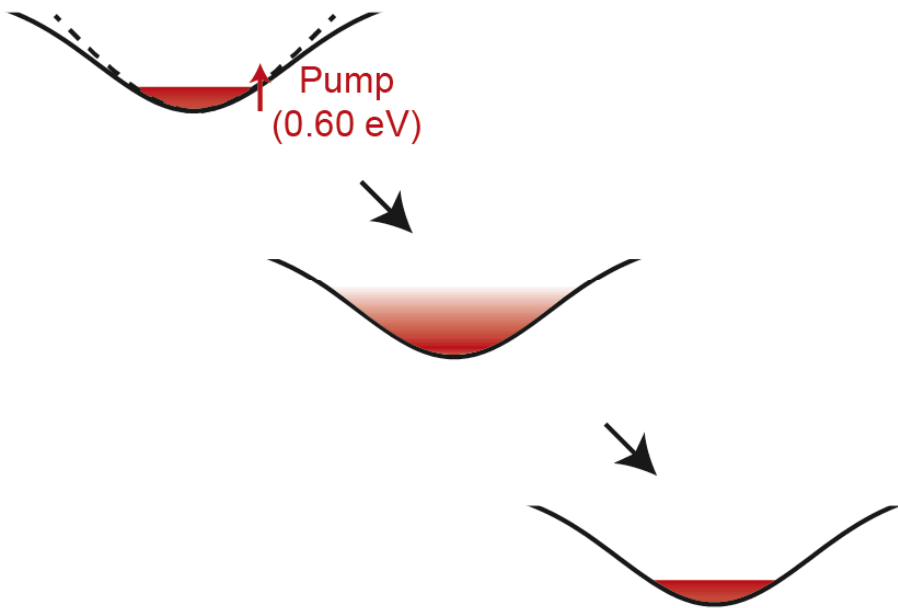


Ultrafast AMPLITUDE SWITCHING of the Perfect Absorber



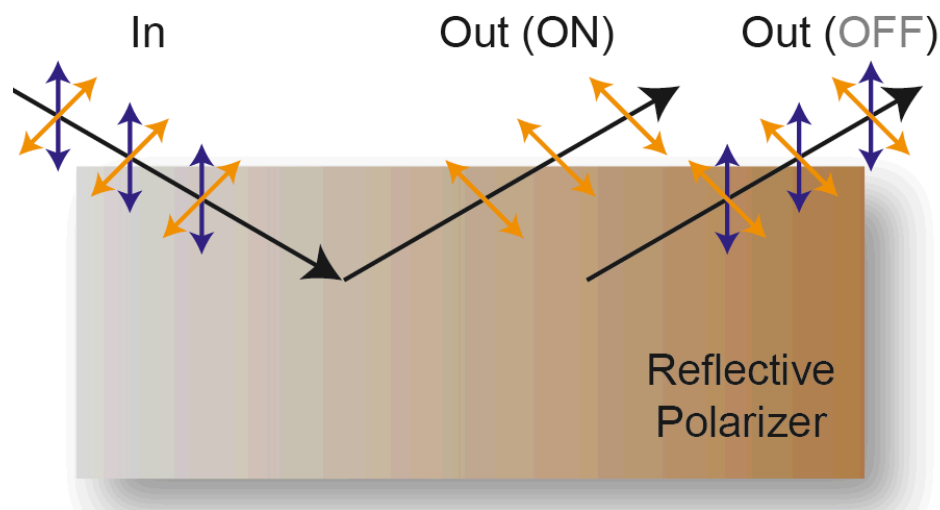
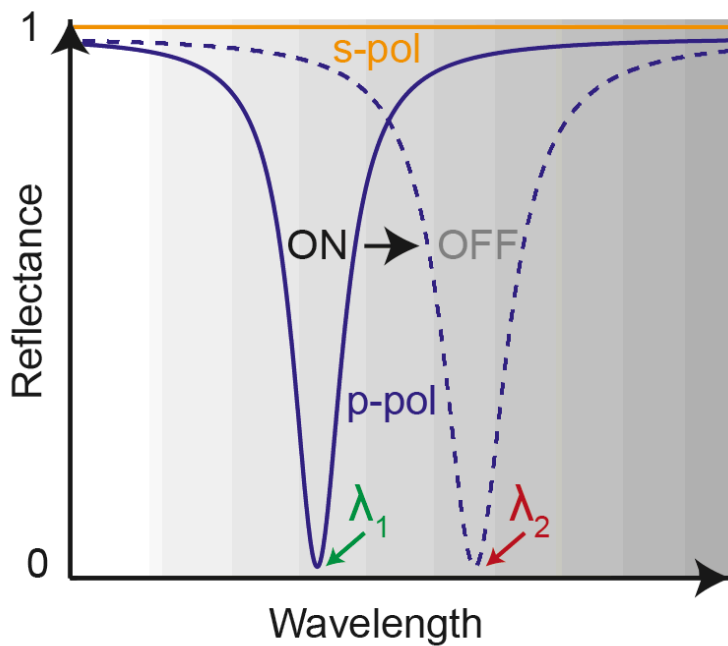


Ultrafast AMPLITUDE SWITCHING of the Perfect Absorber



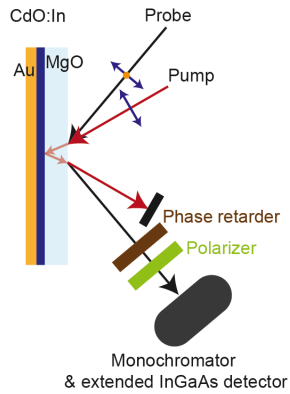


Ultrafast POLARIZATION SWITCHING



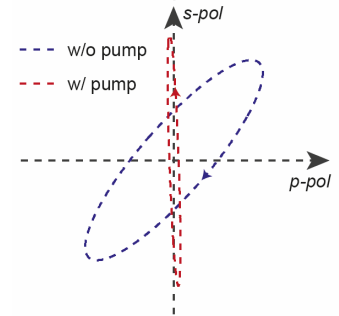
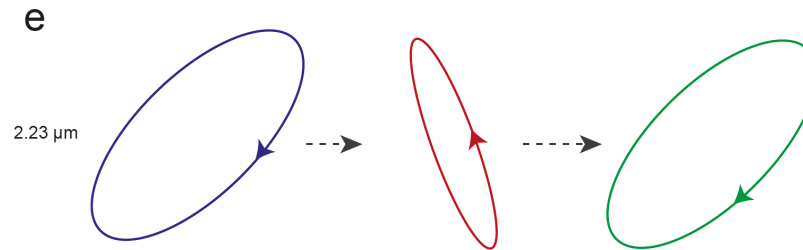
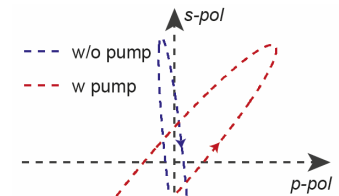
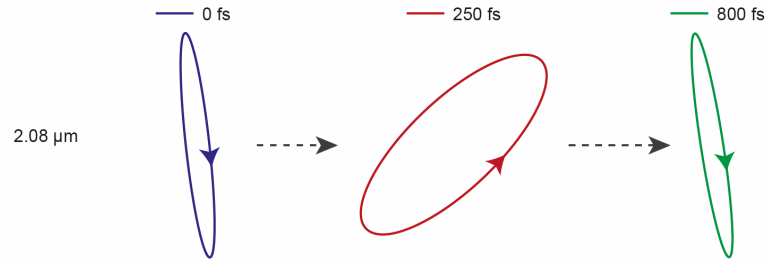


Ultrafast POLARIZATION SWITCHING

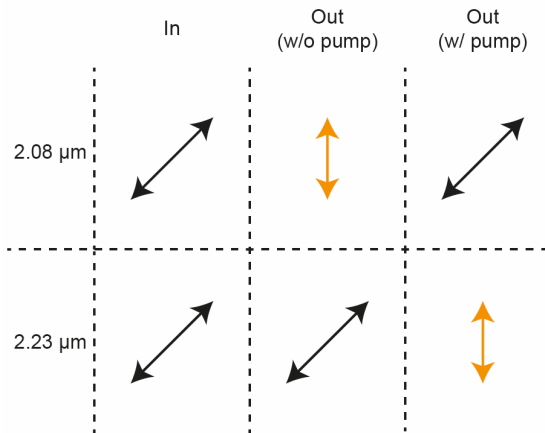


Experiments

Simulations



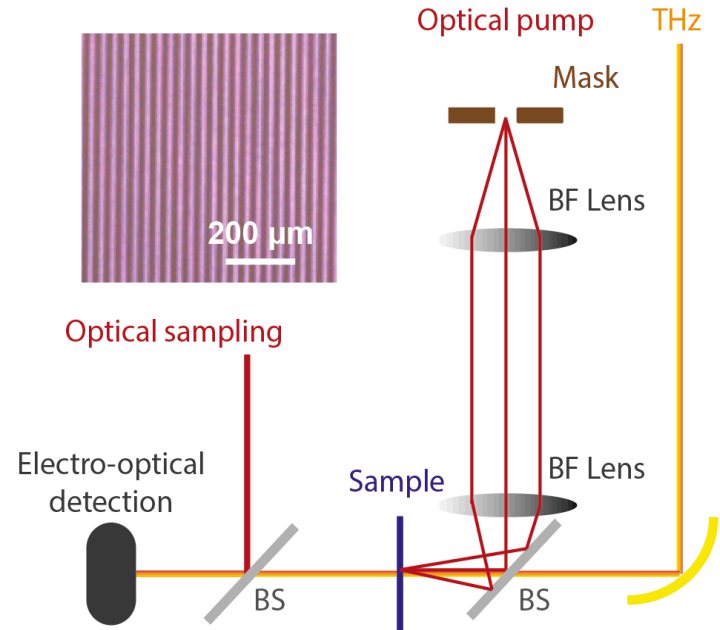
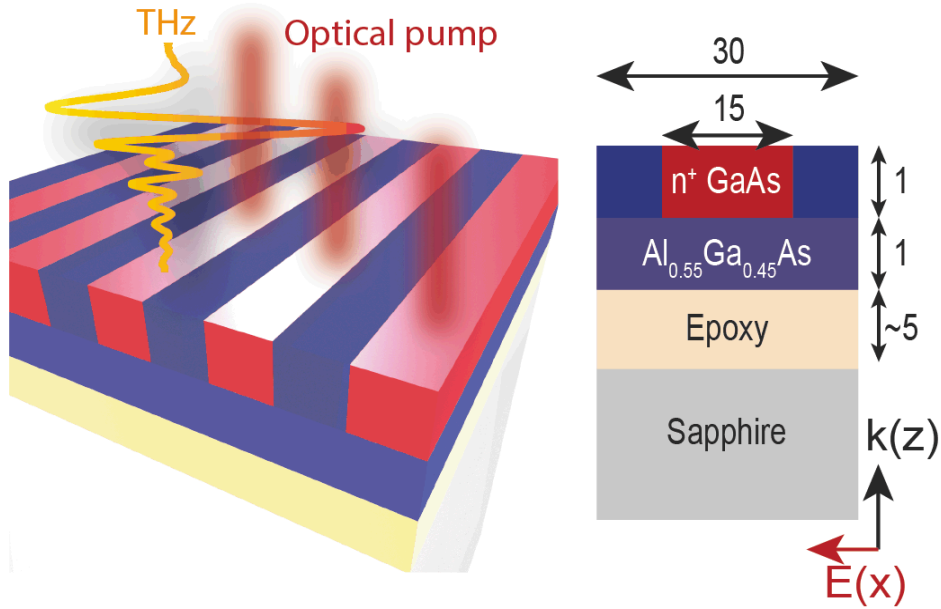
Predicted polarization input/output:

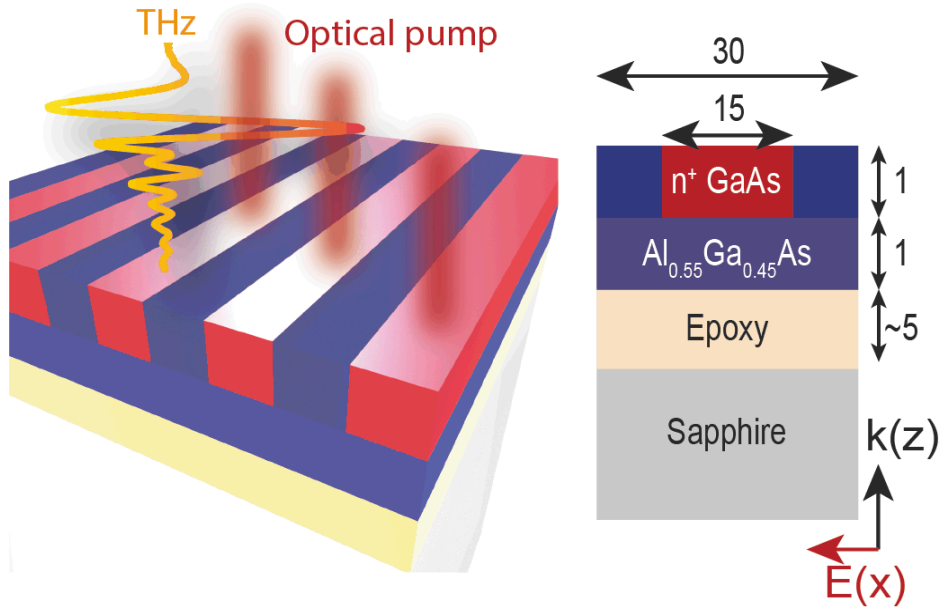




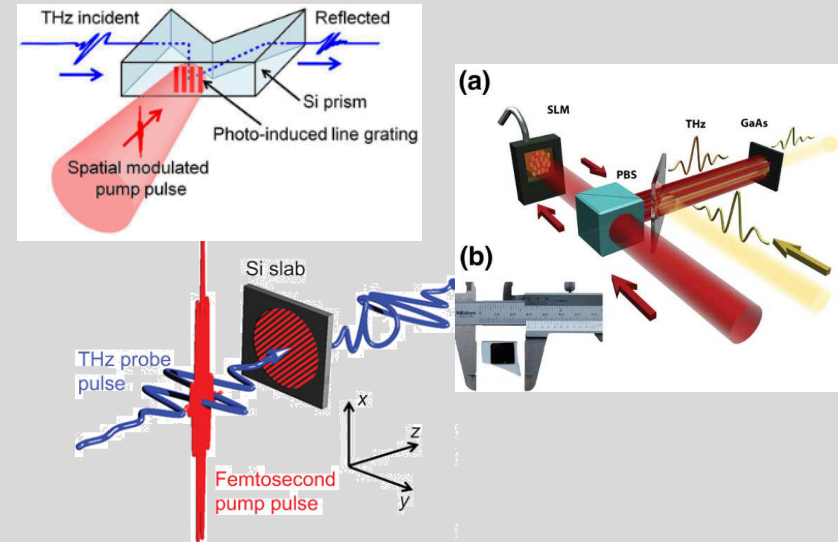
TRANSIENT GaAs Plasmonic Metasurfaces

Structured-optical pump THz probe (S-OPTP):





Structured-optical pump THz probe (S-OPTP):

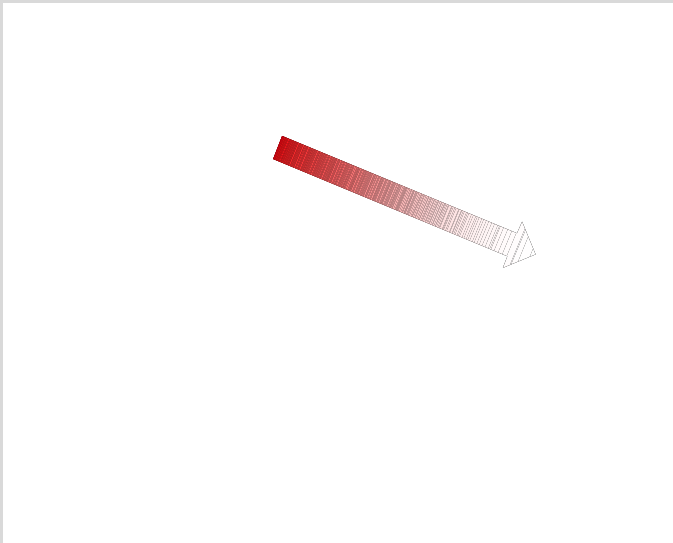


Okada et. al., Sci. Rep. (2011);
 Chatzakis et. al., Appl. Phys. Lett. (2013);
 Kamaraju et. al., Light Sci. App. (2014)
 Georgiou et. al., Sci. Rep. (2014)

- Our **Goals**:
 - Demonstrate a **wide-bandwidth** frequency tuning;
 - Reveal the **ultrafast dynamics** of plasmon formation;



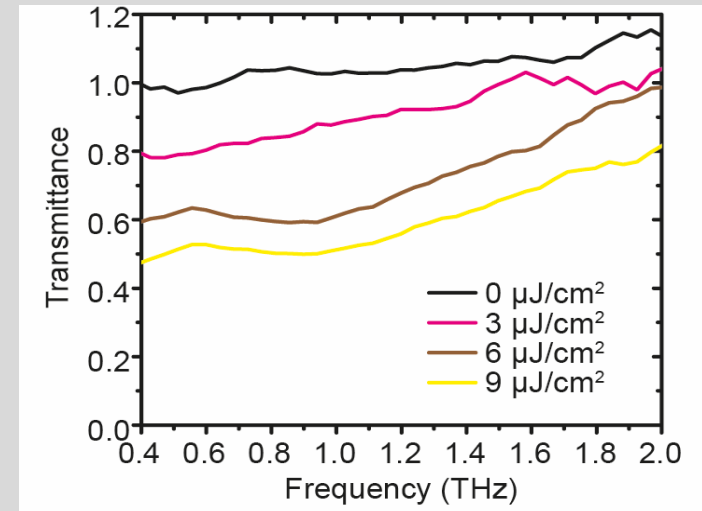
Pump fluence-dependent transmittance (Experiments-Structured Pump)



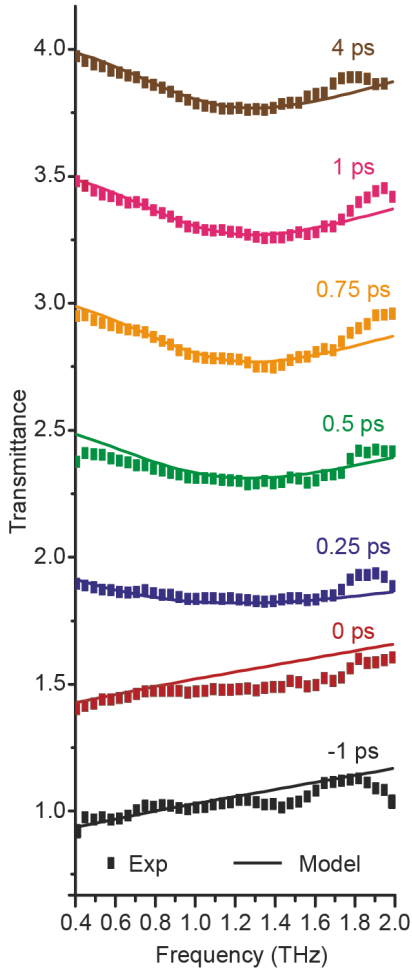
Modulation from **0.5 THz to 1.7 THz**

- One of the **widest dynamic modulation bandwidth** demonstrated (to the best of our knowledge)

Pump fluence-dependent transmittance (Experiments-Unstructured Pump)



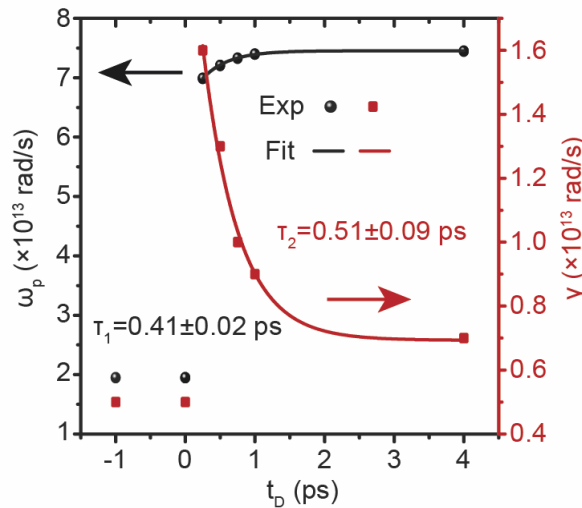
Only Intensity Modulation.



Processes involved:

- (1). Creation of **non-equilibrium** hot electron distribution by the optical pump;
- (2). Hot electron thermalization (**equilibrium** within themselves & Fermi Dirac distribution); **<100 fs**
- (3). Electron-phonon **coupling**. **~500 fs**

$$m^* = \frac{1}{\int f(E,t) \frac{1}{\hbar^2} \frac{d^2 E}{dk^2} dk}, \quad \omega_p = \sqrt{ne^2 / \epsilon_0 m^*}$$



Within the **~500 fs** electron-phonon cooling process:

- Plasma **frequency increases**;
- Plasma **damping decreases**.



Conclusions

- Ultrafast switches using doped CdO
 - High electron mobility oxide
 - High contrast amplitude switch
 - Femtosecond polarization switch
- Transient GaAs metasurface
 - Ultrafast dynamics of plasmon formation
 - THz modulation

Acknowledgement

- CINT (& Sandia)
 - I. Brener, M.B. Sinclair, S. Campione, S. Liu, T.S. Luk, P.Q. Liu
 - J. Reno
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- North Carolina State
 - J-P. Maria, K. Kelley, E. Sachet